

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 8 A, 650 V, D2, DPAK

# FFSD0865B-F085

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Applications**

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

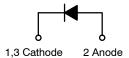
#### MAXIMUM RATINGS (T<sub>.1</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	$V_{RRM}$	650	V	
Single Pulse Avalanche Energy ( $I_{L(pk)} = 11.5 \text{ A}, L = 0.5 \text{ mH}, V = 50$	E <sub>AS</sub>	33	mJ	
Continuous Rectified Forward T <sub>C</sub> < 153		lF	8.0	Α
Current	T <sub>C</sub> < 135		11.6	
Non-Repetitive Peak Forward Surge Current	$T_C = 25^{\circ}C$ , $t_P = 10 \mu s$	I <sub>FM</sub>	577	Α
	$T_{C} = 150^{\circ}C,$ $t_{P} = 10 \ \mu s$		538	
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	$T_C = 25$ °C $t_P = 8.3$ ms	I <sub>FSM</sub>	42	Α
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	91	W
	T <sub>C</sub> = 150°C		15	
Operating Junction and Storage T Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

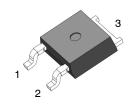
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

V <sub>RRM</sub>	I <sub>F</sub>
650 V	8.0 A

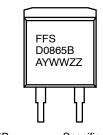


**Schottky Diode** 



DPAK CASE 369AS

#### **MARKING DIAGRAM**



FFSD0865B A Y WW

- Specific Device CodeAssembly Location
- = Year

  W = Work Week
- ZZ = Assembly Lot Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## FFSD0865B-F085

#### THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.64	°C/W

## **ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
ON CHARAC	TERISTICS					
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 25°C	-	1.39	1.7	V
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125°C	-	1.55	2.0	
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 175°C	-	1.71	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>J</sub> = 25°C	-	0.5	40	μΑ
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 125°C	-	1.0	80	
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 175°C	-	2.0	160	
CHARGES, C	APACITANCES & GATE RES	ISTANCE				
$Q_{C}$	Total Capacitive Charge	V <sub>C</sub> = 400 V	-	22	_	nC
C <sub>tot</sub>		V <sub>R</sub> = 1 V, f = 100 kHz	-	336	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	39	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	_	30	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method <sup>†</sup>	Reel Size	Tape Width	Quantity
FFSD0865B-F085	FFSD0865B	DPAK	Tape & Reel	330 mm	16 mm	2500 units

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## FFSD0865B-F085

## **TYPICAL CHARACTERISTICS**

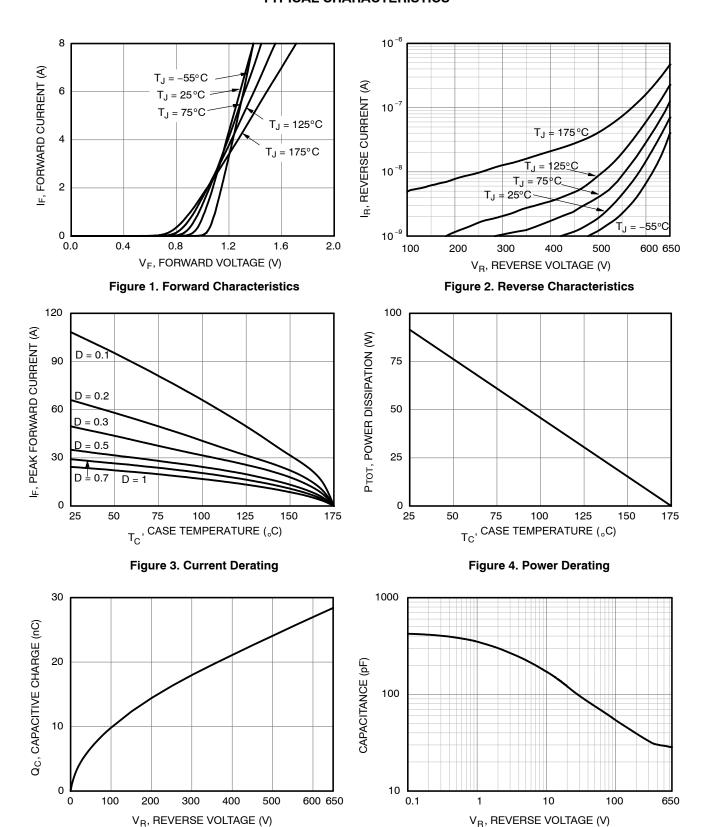


Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

# FFSD0865B-F085

# TYPICAL CHARACTERISTICS (continued)

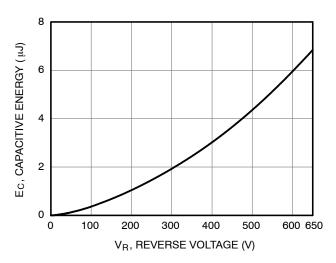


Figure 7. Capacitance Stored Energy

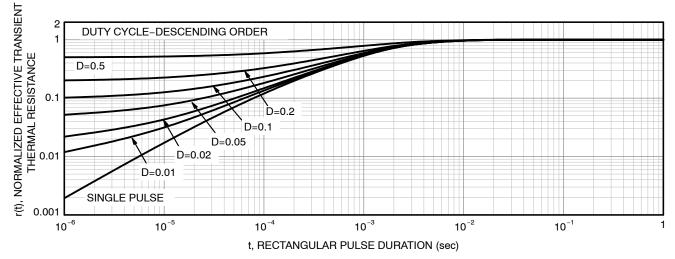


Figure 8. Junction-to-Case Transient Thermal Response

h3

3

-A

L3

Æ

L4





C

(z)

# **DPAK3 (TO-252 3 LD)**CASE 369AS **ISSUE A**

**DATE 28 SEP 2022** 

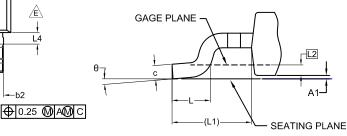
MILLIMETERS

NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
- CORNERS OR EDGE PROTRUSION.

  FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX.

  F) DIMENSIONS ARE EXCLUSIVE OF BURRS,
- MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



**DETAIL A** (ROTATED -90°) SCALE: 12X

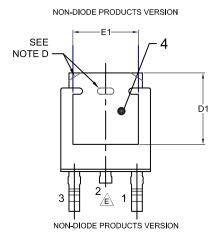
	MIN.	NOM.	MAX.	
Α	2.18	2.29	2.39	
A1	0.00	-	0.127	
b	0.64	0.77	0.89	
b2	0.76	0.95	1.14	
b3	5.21	5.34	5.46	
С	0.45	0.53	0.61	
c2	0.45	0.52	0.58	
D	5.97	6.10	6.22	
D1	5.21	_	_	
Е	6.35	6.54	6.73	
E1	4.32	_	_	
е	2.286 BSC			
e1	4.572 BSC			
Н	9.40	9.91	10.41	
L	1.40	1.59	1.78	
L1	2.90 REF			
12	0.51 BSC			

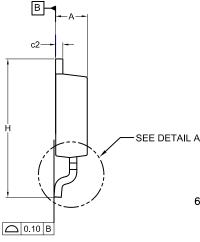
0.89

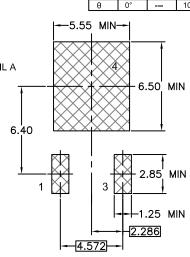
1.08

1.27

1.02







L4

## **GENERIC MARKING DIAGRAM\***

XXXXXX XXXXXX **AYWWZZ** 

XXXX = Specific Device Code

= Assembly Location Α

WW = Work Week

= Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

## LAND PATTERN RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	DPAK3 (TO-252 3 LD)		PAGE 1 OF 1	

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